AOTS26108

30V/20V Complementary MOSFET

General Description

- Trench Power MOSFET technology
- Low $R_{DS(ON)}$
- Low Gate Charge
- RoHS and Halogen-Free Compliant

Applications

- This device is ideal for Load Switch

Product Summary

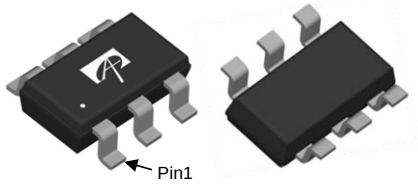
N-Channel	P-Channel
V_{DS}= 30V	-20V
I_D= 3.8A (V_{GS}=10V)	-4.5A (V_{GS}=-4.5V)
$R_{DS(ON)}$	$R_{DS(ON)}$
< 50mΩ (V_{GS}=10V)	< 44mΩ (V_{GS}=-4.5V)
< 57mΩ (V_{GS}=4.5V)	< 59mΩ (V_{GS}=-2.5V)
< 72mΩ (V_{GS}=2.5V)	< 80mΩ (V_{GS}=-1.8V)

ESD protection

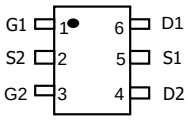
Green Product

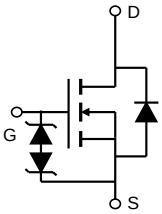
TSOP6

Top View Bottom View

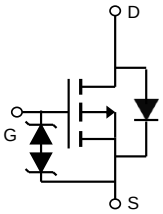


Top View





n-channel



p-channel

Absolute Maximum Ratings T_A=25°C unless otherwise noted

Parameter		Symbol	Max n-channel	Max p-channel	Units
Drain-Source Voltage		V_{DS}	30	-20	V
Gate-Source Voltage		V_{GS}	±12	±8	V
Continuous Drain Current	T_A=25°C	I_D	3.8	-4.5	A
	T_A=70°C		3	-3.6	
Pulsed Drain Current [C]		I_{DM}	15	-18	
Power Dissipation [B]	T_A=25°C	P_D	1.25	1.25	W
	T_A=70°C		0.80	0.80	
Junction and Storage Temperature Range		T_J, T_{STG}	-55 to 150		°C

Thermal Characteristics

Parameter		Symbol	Typ	Max	Units
Maximum Junction-to-Ambient [A]	t ≤ 10s	$R_{\theta JA}$	75	100	°C/W
Maximum Junction-to-Ambient [A D]	Steady-State		105	130	°C/W
Maximum Junction-to-Lead	Steady-State	$R_{\theta JL}$	50	65	°C/W

N-Channel Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	I_D=250µA, V_{GS}=0V	30			V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=30V, V_{GS}=0V			1	µA
		T_J=55°C			5	
I_{GSS}	Gate-Body leakage current	V_{DS}=0V, V_{GS}=±12V			±10	µA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D=250µA	0.5	1	1.5	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=10V, I_D=3.8A		40	50	mΩ
		T_J=125°C		58	73	
		V_{GS}=4.5V, I_D=3.6A		42	57	mΩ
		V_{GS}=2.5V, I_D=3.2A		50	72	mΩ
g_{FS}	Forward Transconductance	V_{DS}=5V, I_D=3.8A		20		S
V_{SD}	Diode Forward Voltage	I_S=1A, V_{GS}=0V		0.7	1	V
I_S	Maximum Body-Diode Continuous Current				1.5	A
DYNAMIC PARAMETERS						
C_{iss}	Input Capacitance	V_{GS}=0V, V_{DS}=15V, f=1MHz		340		pF
C_{oss}	Output Capacitance			30		pF
C_{rss}	Reverse Transfer Capacitance			25		pF
R_g	Gate resistance	f=1MHz	4	8	12	Ω
SWITCHING PARAMETERS						
Q_g(10V)	Total Gate Charge	V_{GS}=10V, V_{DS}=15V, I_D=3.8A		8	16	nC
Q_g(4.5V)	Total Gate Charge			4	8	nC
Q_{gs}	Gate Source Charge			1		nC
Q_{gd}	Gate Drain Charge			1.2		nC
$t_{D(on)}$	Turn-On DelayTime	V_{GS}=10V, V_{DS}=15V, R_L=3.95Ω, R_{GEN}=3Ω		2.5		ns
t_r	Turn-On Rise Time			3		ns
$t_{D(off)}$	Turn-Off DelayTime			30		ns
t_f	Turn-Off Fall Time			5		ns
t_{rr}	Body Diode Reverse Recovery Time	I_F=3.8A, di/dt=500A/µs		5.5		ns
Q_{rr}	Body Diode Reverse Recovery Charge	I_F=3.8A, di/dt=500A/µs		4		nC

A. The value of $R_{\theta JA}$ is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A =25° C. The value in any given application depends on the user's specific board design.
B. The power dissipation P_D is based on $T_{J(MAX)}$=150° C, using ≤ 10s junction-to-ambient thermal resistance.
C. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}$=150° C. Ratings are based on low frequency and duty cycles to keep initialT_J=25° C.
D. The $R_{\theta JA}$ is the sum of the thermal impedence from junction to lead $R_{\theta JL}$ and lead to ambient.
E. The static characteristics in Figures 1 to 6 are obtained using <300µs pulses, duty cycle 0.5% max.
F. These curves are based on the junction-to-ambient thermal impedence which is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, assuming a maximum junction temperature of $T_{J(MAX)}$=150° C. The SOA curve provides a single pulse rating.

N-Channel: TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

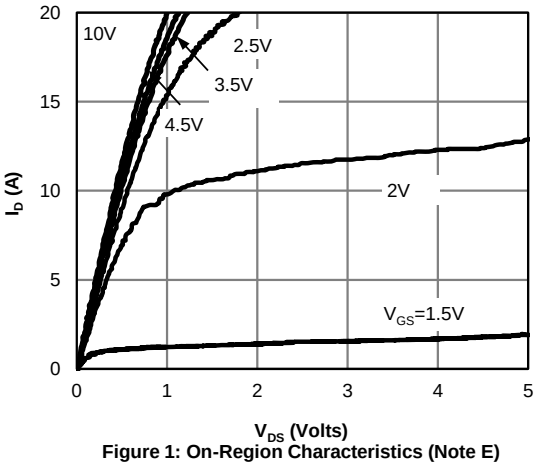


Figure 1: On-Region Characteristics (Note E)

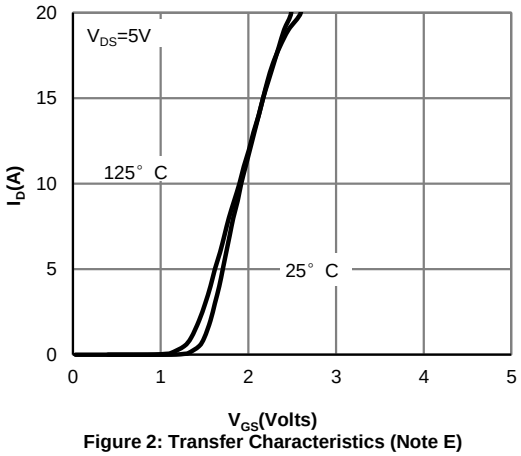


Figure 2: Transfer Characteristics (Note E)

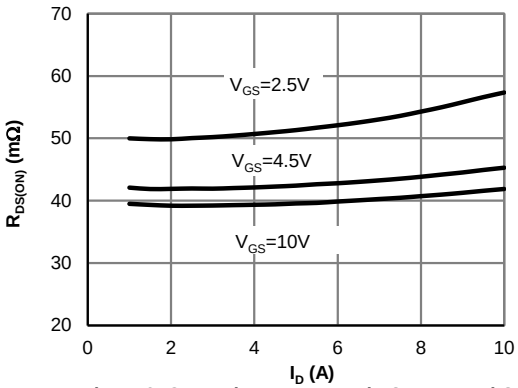


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

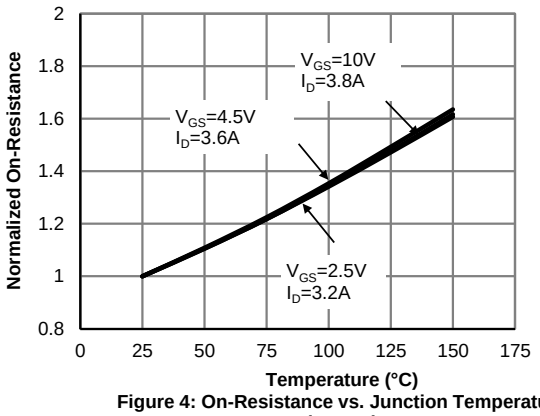


Figure 4: On-Resistance vs. Junction Temperature (Note E)

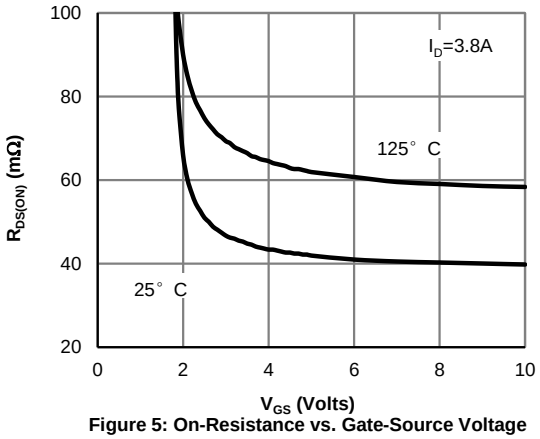


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

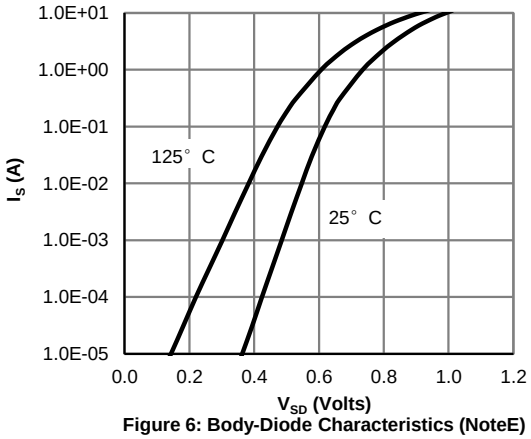


Figure 6: Body-Diode Characteristics (NoteE)

N-Channel: TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

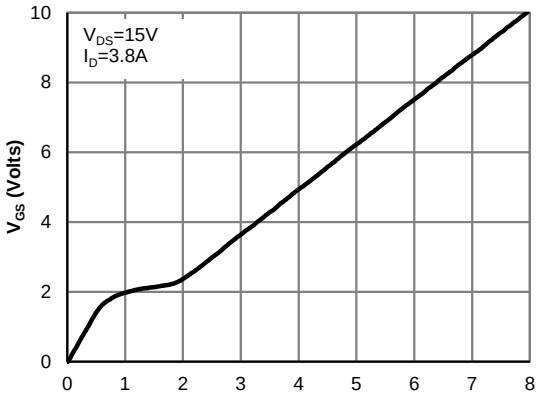


Figure 7: Gate-Charge Characteristics

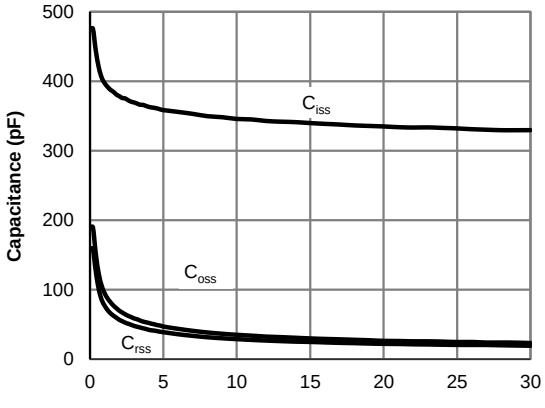
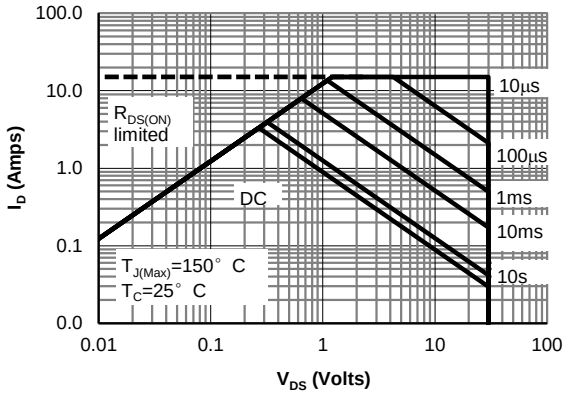


Figure 8: Capacitance Characteristics



V_{GS}> or equal to -2.5V
Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

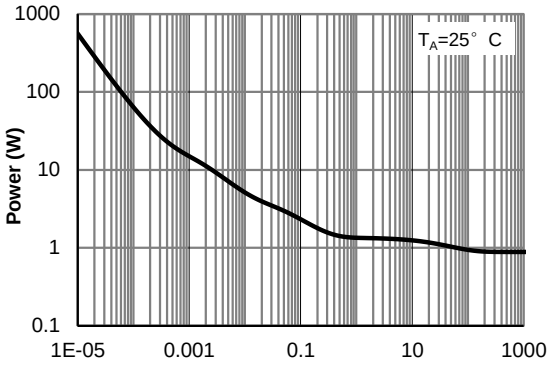


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note F)

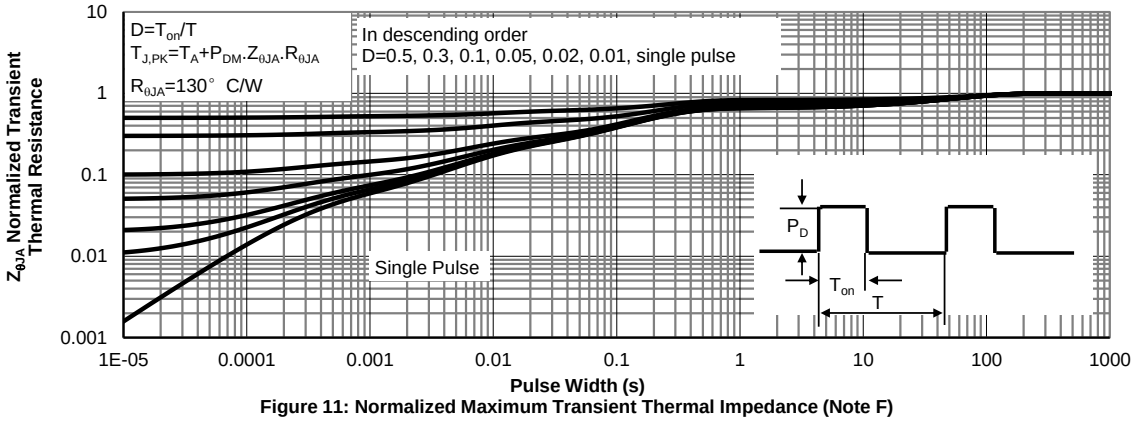
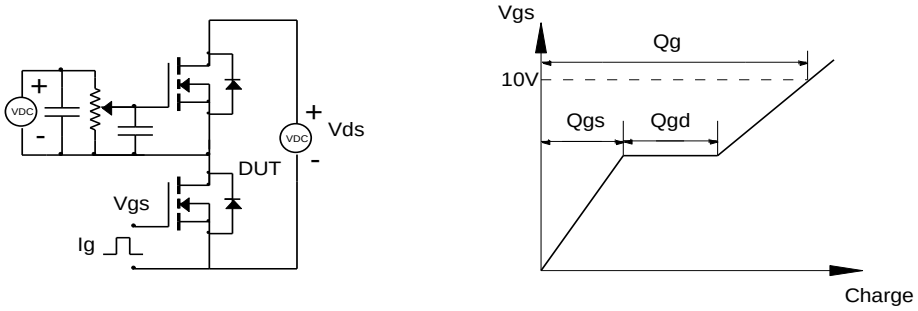
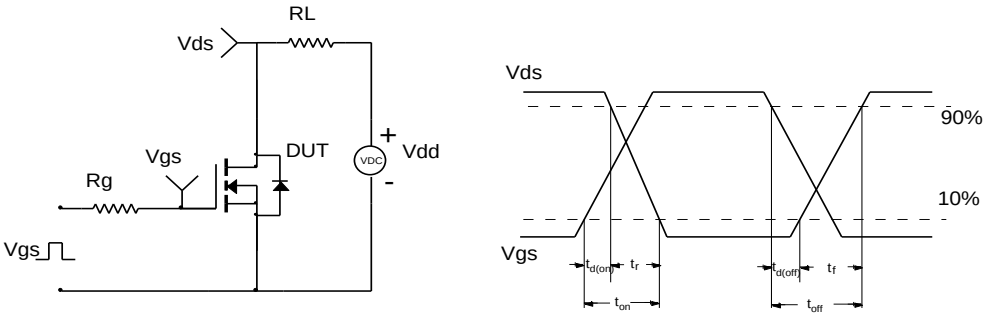


Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)

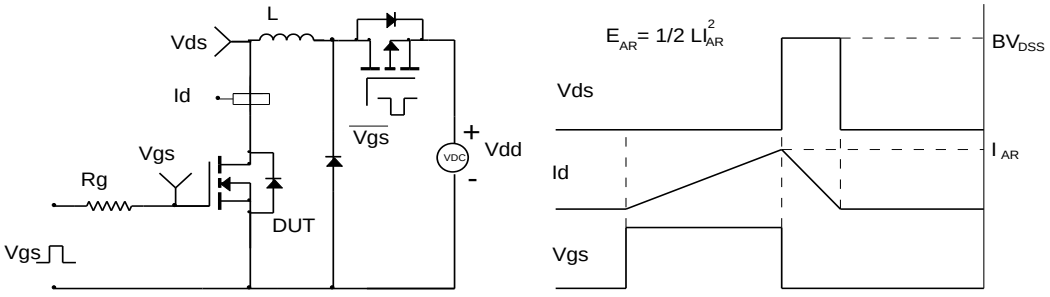
Gate Charge Test Circuit & Waveform



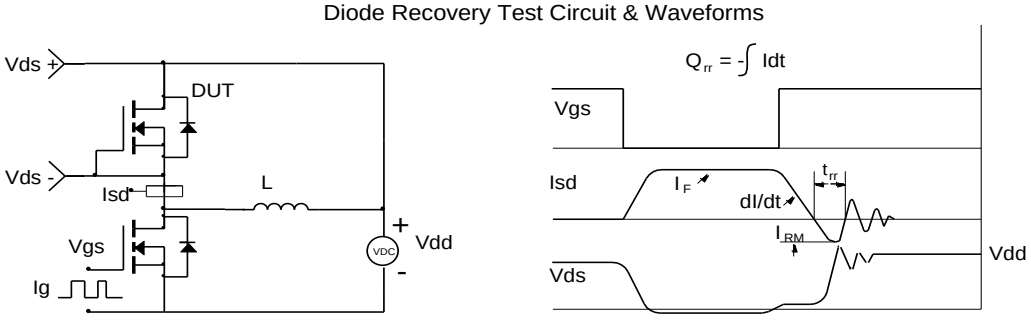
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



P-Channel Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	I_D=-250µA, V_{GS}=0V	-20			V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=-20V, V_{GS}=0V			-1	µA
		T_J=55°C			-5	
I_{GSS}	Gate-Body leakage current	V_{DS}=0V, V_{GS}=±8V			±10	µA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D=-250µA	-0.15	-0.55	-0.95	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=-4.5V, I_D=-4.5A		36	44	mΩ
		T_J=125°C		46	56	
		V_{GS}=-2.5V, I_D=-4A		46	59	mΩ
		V_{GS}=-1.8V, I_D=-3A		60	80	mΩ
g_{FS}	Forward Transconductance	V_{DS}=-5V, I_D=-4.5A		26		S
V_{SD}	Diode Forward Voltage	I_S=-1A, V_{GS}=0V		-0.7	-1	V
I_S	Maximum Body-Diode Continuous Current				-2	A
DYNAMIC PARAMETERS						
C_{iss}	Input Capacitance	V_{GS}=0V, V_{DS}=-10V, f=1MHz		930		pF
C_{oss}	Output Capacitance			90		pF
C_{rss}	Reverse Transfer Capacitance			80		pF
R_g	Gate resistance	V_{GS}=0V, V_{DS}=0V, f=1MHz		15	30	Ω
SWITCHING PARAMETERS						
Q_g(4.5V)	Total Gate Charge	V_{GS}=-4.5V, V_{DS}=-10V, I_D=-4.5A		8.5	17	nC
Q_{gs}	Gate Source Charge			1		nC
Q_{gd}	Gate Drain Charge			2.5		nC
$t_{D(on)}$	Turn-On DelayTime	V_{GS}=-4.5V, V_{DS}=-10V, R_L=2.22Ω, R_{GEN}=3Ω		12		ns
t_r	Turn-On Rise Time			11		ns
$t_{D(off)}$	Turn-Off DelayTime			82		ns
t_f	Turn-Off Fall Time			35		ns
t_{rr}	Body Diode Reverse Recovery Time	I_F=-4.5A, di/dt=500A/µs		25		ns
Q_{rr}	Body Diode Reverse Recovery Charge	I_F=-4.5A, di/dt=500A/µs		37		nC

A. The value of $R_{\theta JA}$ is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A =25° C. The value in any given application depends on the user's specific board design.
B. The power dissipation P_D is based on $T_{J(MAX)}$=150° C, using ≤ 10s junction-to-ambient thermal resistance.
C. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}$=150° C. Ratings are based on low frequency and duty cycles to keep initialT_J=25° C.
D. The $R_{\theta JA}$ is the sum of the thermal impedence from junction to lead $R_{\theta JL}$ and lead to ambient.
E. The static characteristics in Figures 1 to 6 are obtained using <300µs pulses, duty cycle 0.5% max.
F. These curves are based on the junction-to-ambient thermal impedence which is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, assuming a maximum junction temperature of $T_{J(MAX)}$=150° C. The SOA curve provides a single pulse rating.

P-Channel: TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

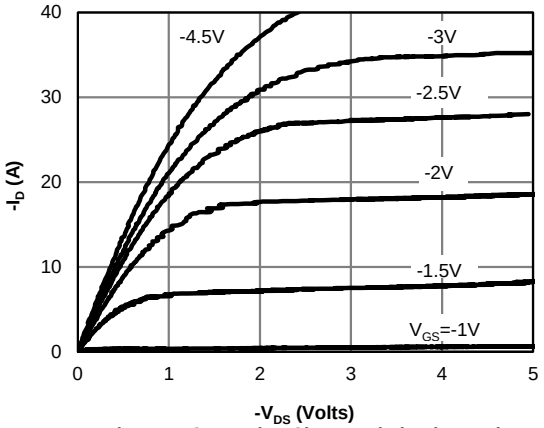


Figure 1: On-Region Characteristics (Note E)

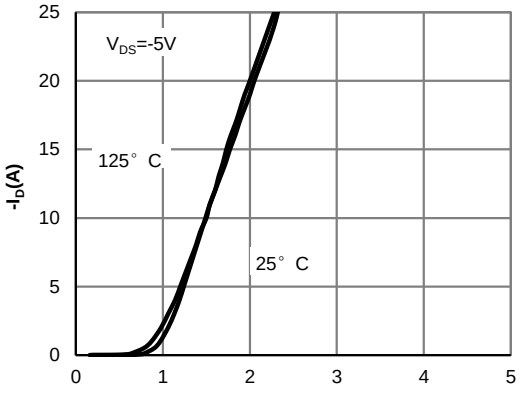


Figure 2: Transfer Characteristics (Note E)

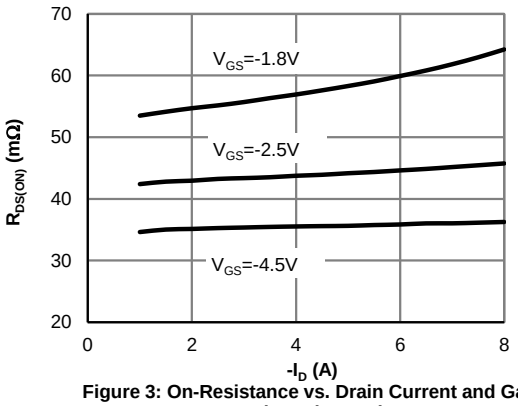


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

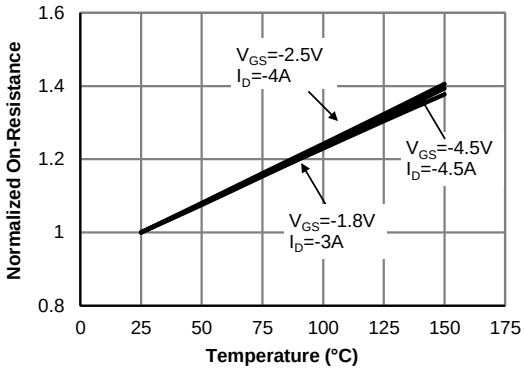


Figure 4: On-Resistance vs. Junction Temperature (Note E)

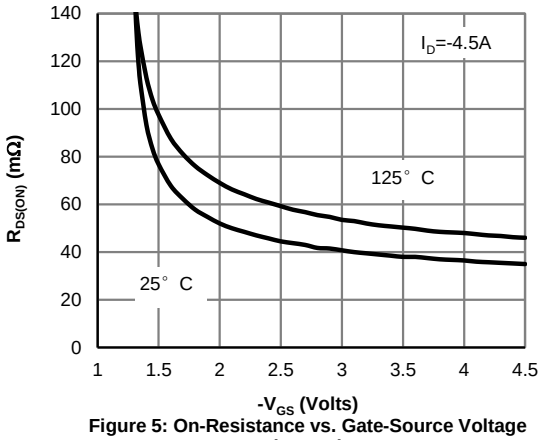


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

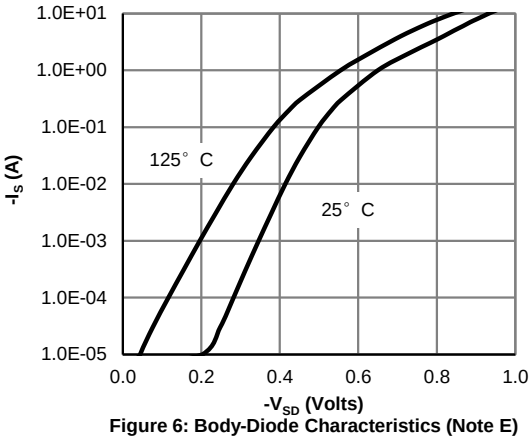


Figure 6: Body-Diode Characteristics (Note E)

P-Channel: TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

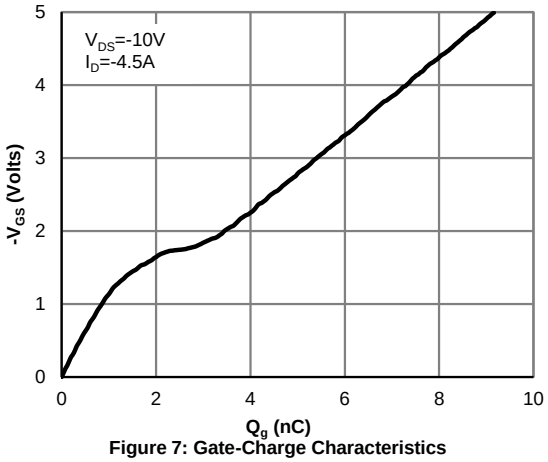


Figure 7: Gate-Charge Characteristics

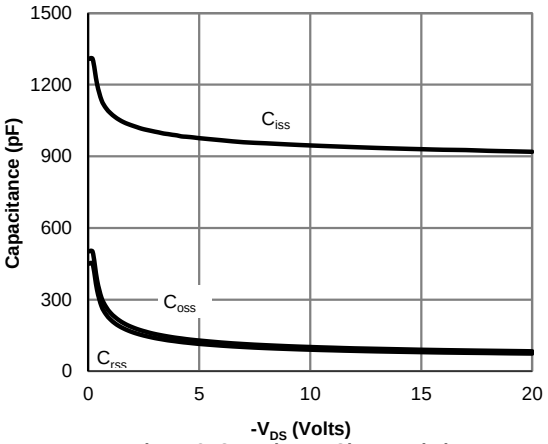
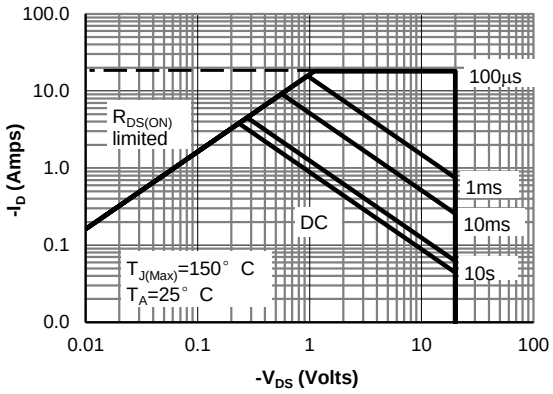


Figure 8: Capacitance Characteristics



V_{GS}> or equal to -1.8V
Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

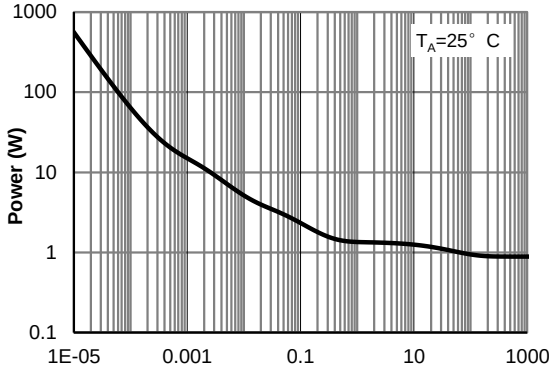


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note F)

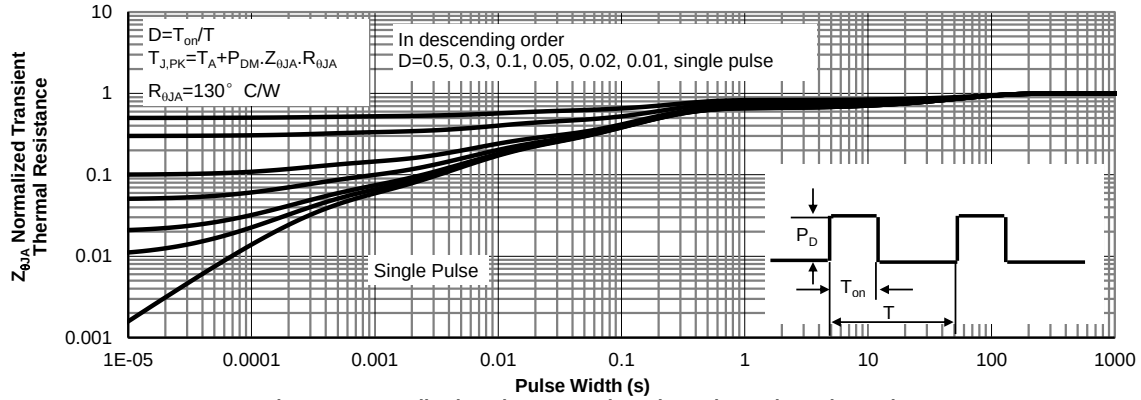
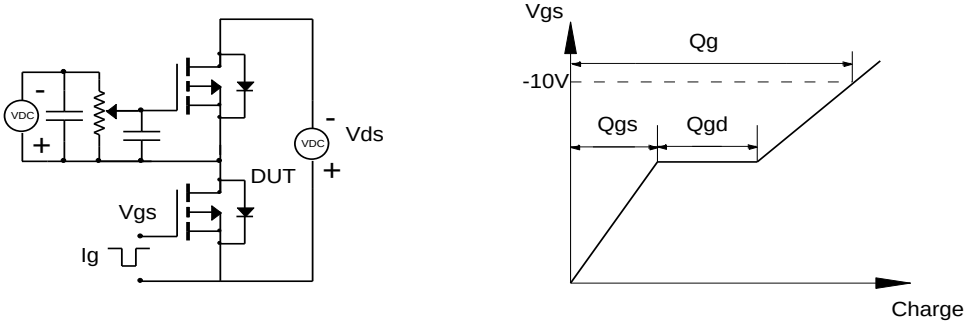
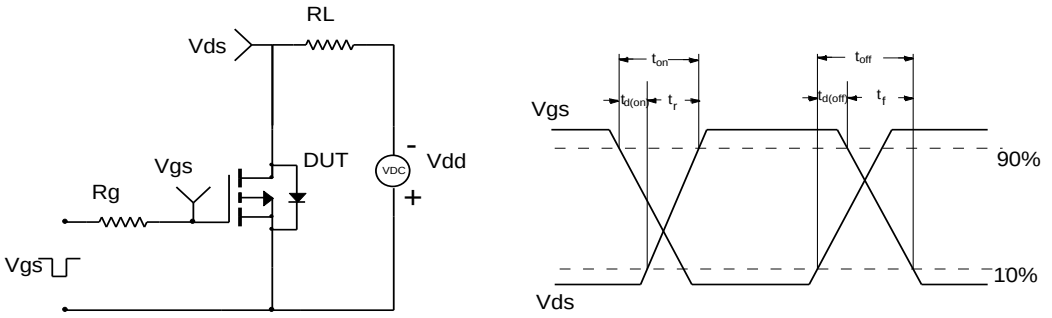


Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)

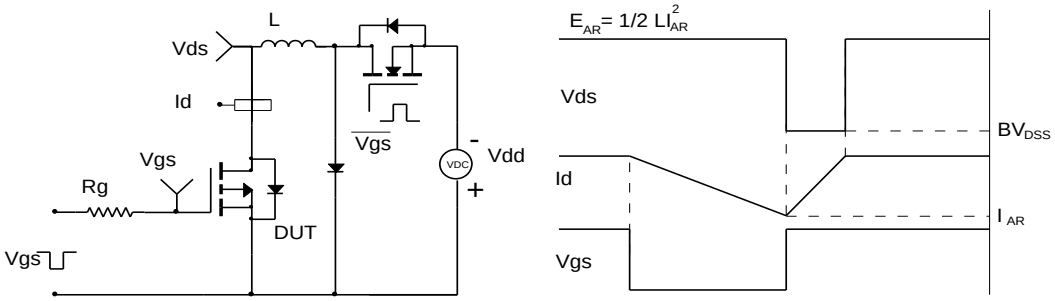
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms